

Dual N-Channel Advanced Power MOSFET

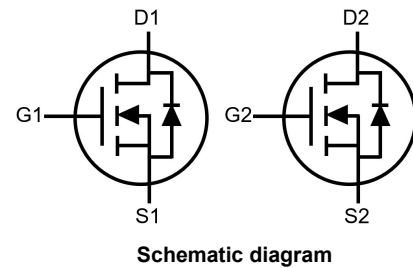
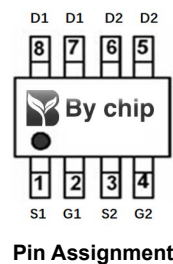
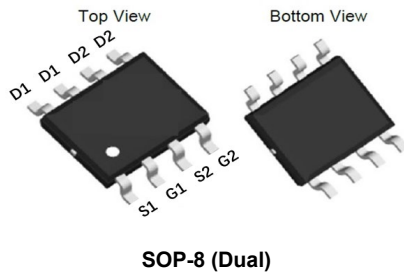
Features

- $V_{DS} = 60V$, $I_D = 5A$
 $R_{DS(ON)} < 30\text{ m}\Omega$ @ $V_{GS} = 10V$
 $R_{DS(ON)} < 36\text{ m}\Omega$ @ $V_{GS} = 4.5V$

General Features

- Advanced Trench Technology
- Provide Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free and Green Available

100% UIS TESTED!
 100% ΔV_{ds} TESTED!



Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Max.	Units
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	$T_A = 25^\circ\text{C}$	5
		$T_A = 100^\circ\text{C}$	3.3
I_{DM}	Pulsed Drain Current ^{note1}	20	A
EAS	Single Pulsed Avalanche Energy ^{note2}	20	mJ
P_D	Power Dissipation	$T_A = 25^\circ\text{C}$	1.74
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	72	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS} = 0V,$	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS} = \pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0		2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=10V, I_D=5A$	-		30	m Ω
		$V_{GS}=4.5V, I_D=3A$	-		36	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0MHz$	-	853	-	pF
C_{oss}	Output Capacitance		-	60	-	pF
C_{riss}	Reverse Transfer Capacitance		-	29	-	pF
Q_g	Total Gate Charge	$V_{DD}=30V, I_D=2.5A,$ $V_{GS}=10V$	-	20	-	nC
Q_{gs}	Gate-Source Charge		-	3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	4.5	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, I_D=5A,$ $R_{GEN}=1.8\Omega, V_{GS}=10V$	-	6	-	ns
t_r	Turn-on Rise Time		-	6	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	19	-	ns
t_f	Turn-off Fall Time		-	2.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time	$I_F=5A, di/dt=100A/\mu s$	-	13	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	9	-	nC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

 2. EAS condition :Starting $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_{GS}=10V, L=0.5mH, R_g=25\Omega, I_{AS}=9A$

 3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 0.5\%$

Typical Performance Characteristics

Figure 1: Output Characteristics

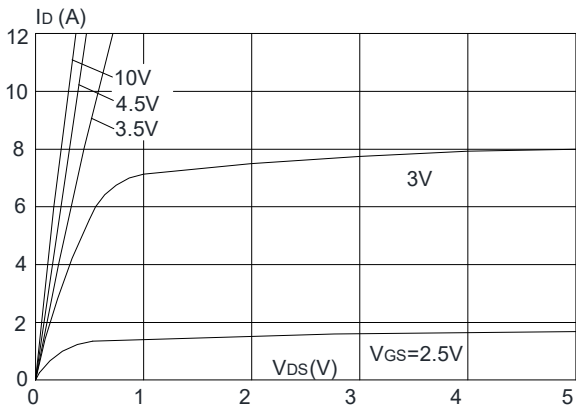


Figure 2: Typical Transfer Characteristics

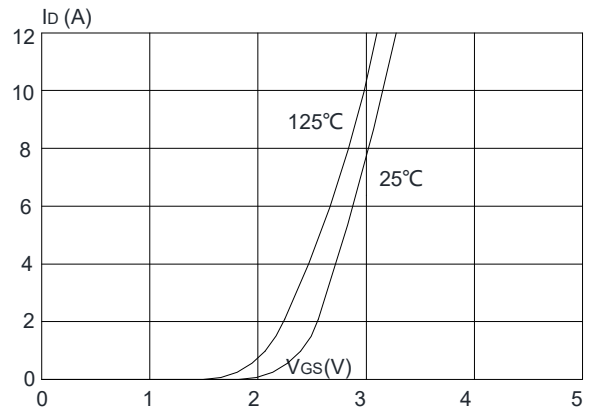


Figure 3: On-resistance vs. Drain Current

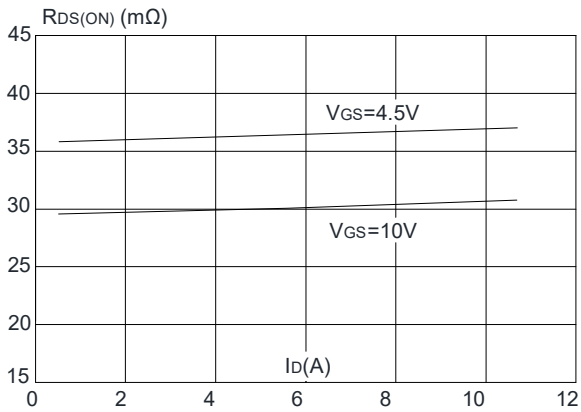


Figure 4: Body Diode Characteristics

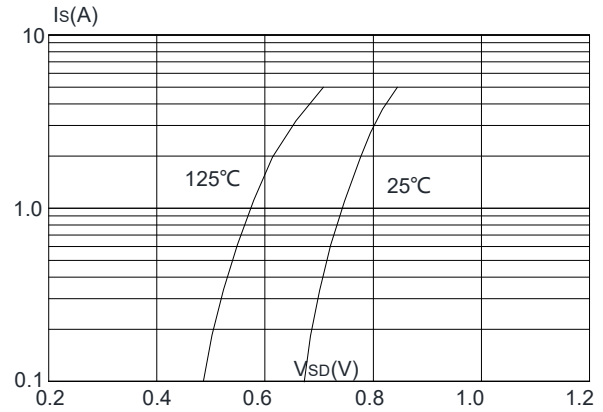


Figure 5: Gate Charge Characteristics

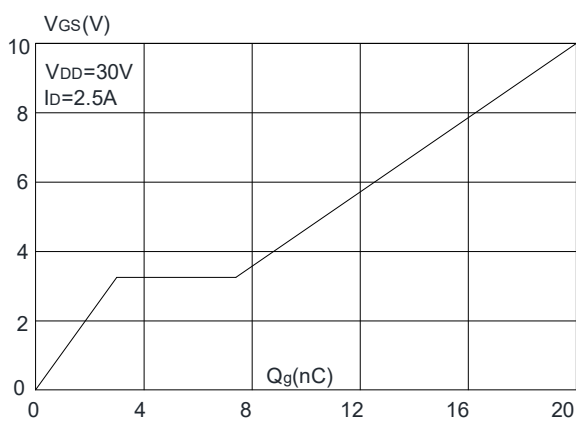


Figure 6: Capacitance Characteristics

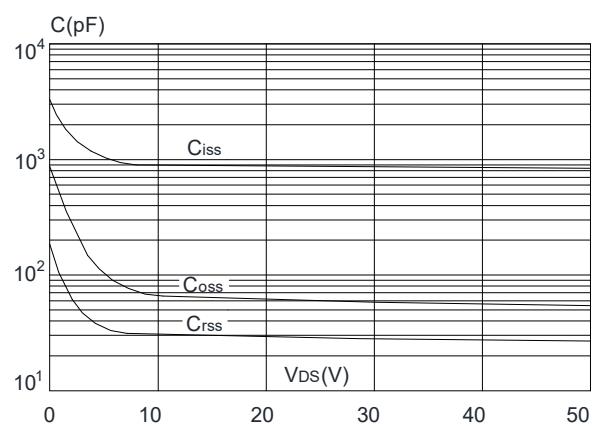


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

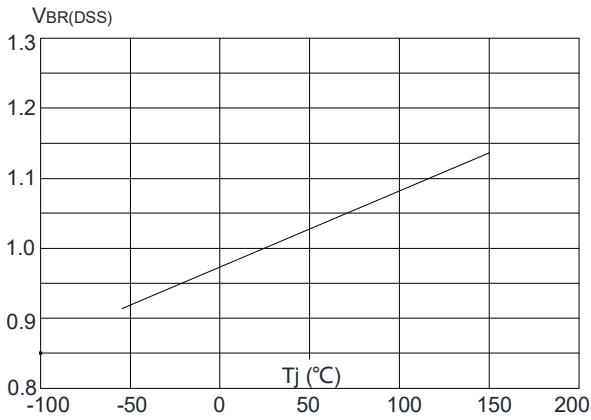


Figure 8: Normalized on Resistance vs. Junction Temperature

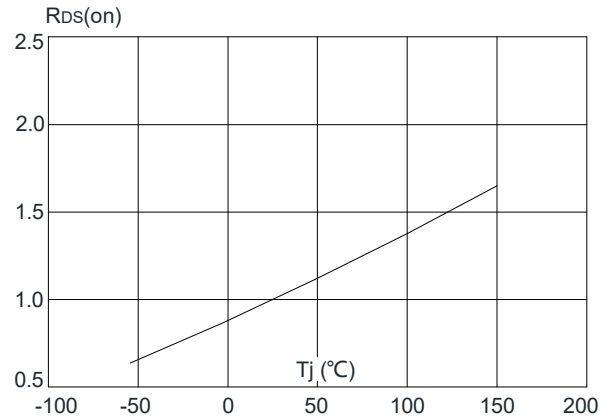


Figure 9: Maximum Safe Operating Area

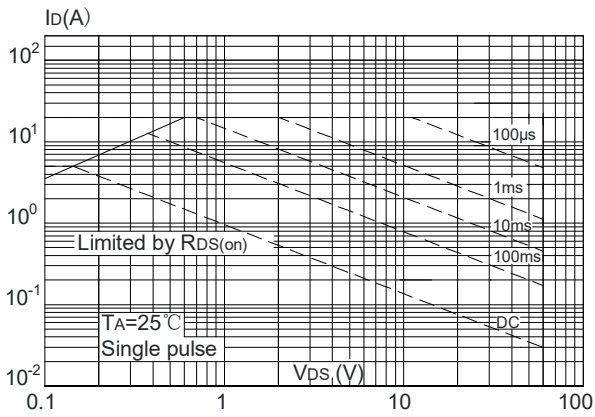


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

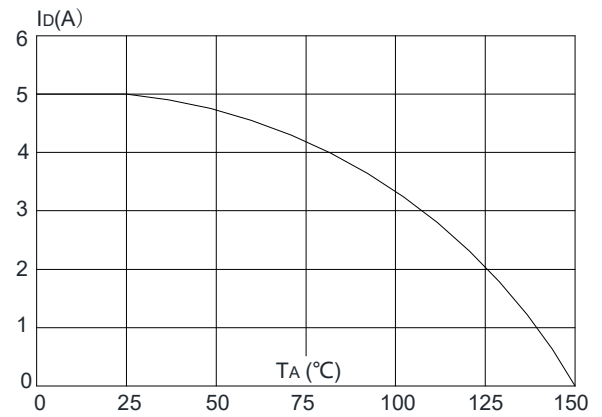
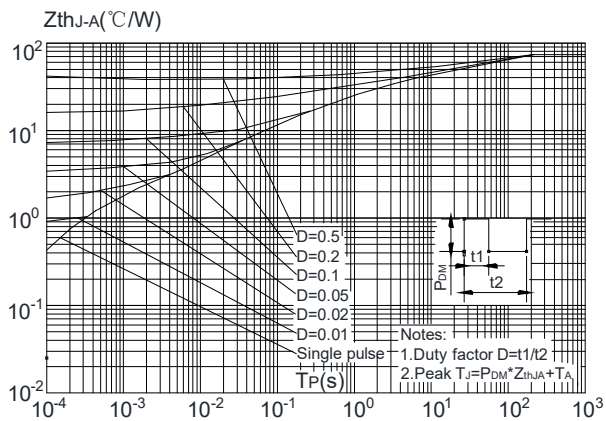


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Test Circuit



Figure1:Gate Charge Test Circuit & Waveform

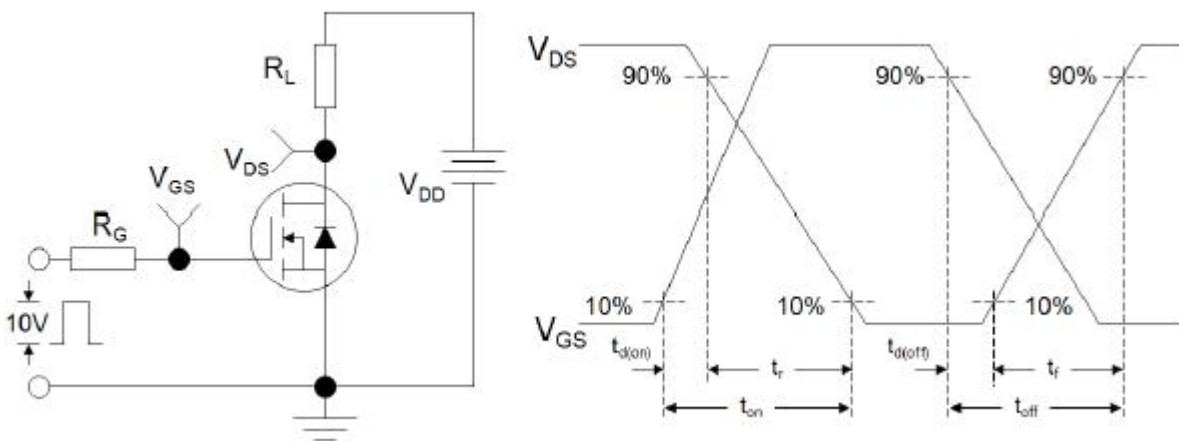


Figure 2: Resistive Switching Test Circuit & Waveforms

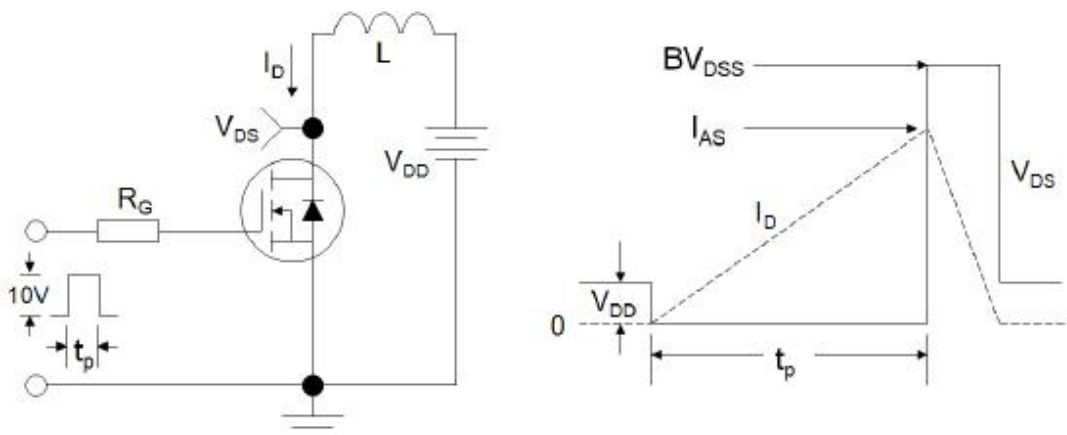


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms